

# **PSMN5R0-100ES**

# N-channel 100 V 5 m $\Omega$ standard level MOSFET in I2PAK

Rev. 3 — 26 September 2011

Product data sheet

## 1. Product profile

## 1.1 General description

Standard level N-channel MOSFET in a I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

## 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

	• • • • • • • • • • • • • • • • • • • •						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	[1]	-	-	120	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	338	W
T <sub>j</sub>	junction temperature			-55	-	175	°C
Static char	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{see } \frac{\text{Figure 13}}{\text{Figure 13}}}$		-	7.7	9	mΩ
		$V_{GS} = 10 \text{ V; } I_D = 25 \text{ A;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure } 13}{\text{ or } 13}$	[2]	-	4.3	5	mΩ
Dynamic c	haracteristics						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 75 \text{ A};$		-	49	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 50 V; see <u>Figure 14</u> ; see <u>Figure 15</u>		-	170	-	nC
Avalanche ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} &V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C;} \\ &I_D = 120 \text{ A; } V_{sup} \leq 100 \text{ V;} \\ &R_{GS} = 50 \Omega; \text{ Unclamped} \end{split}$		-	-	537	mJ



- [1] Continuous current limited by package.
- [2] Measured 3 mm from package.

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT226 (I2PAK)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN5R0-100ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

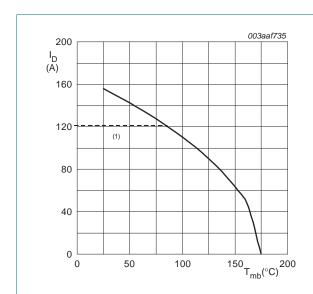
# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	100	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ		-	100	V
$V_{GS}$	gate-source voltage			-20	20	V
$I_D$	drain current	$V_{GS} = 10 \text{ V; } T_j = 100 \text{ °C; see } \frac{\text{Figure 1}}{}$		-	110	Α
		$V_{GS} = 10 \text{ V; } T_{mb} = 25 \text{ °C; see } \frac{\text{Figure 1}}{}$	[1]	-	120	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 3		-	622	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	338	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-dr	ain diode					
Is	source current	T <sub>mb</sub> = 25 °C	<u>[1]</u>	-	120	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	622	Α
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 120 A; $V_{sup}$ ≤ 100 V; $R_{GS}$ = 50 $\Omega$ ; Unclamped		-	537	mJ

#### [1] Continuous current limited by package



 $V_{GS} \ge 10 \text{ V}$ ; (1) capped at 120 A due to package.

Fig 1. Continuous drain current as a function of mounting base temperature

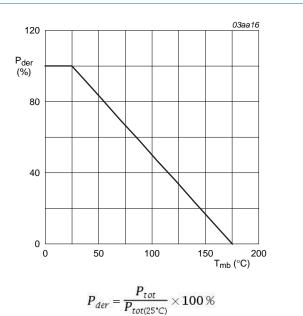
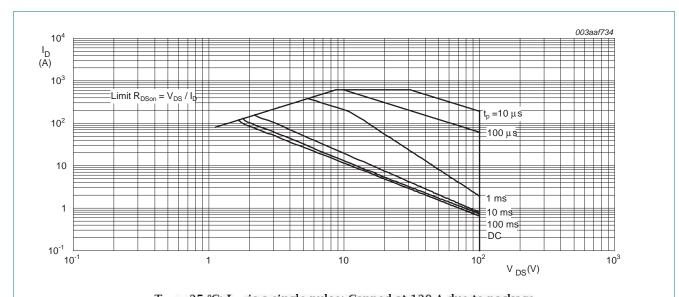


Fig 2. Normalized total power dissipation as a function of mounting base temperature



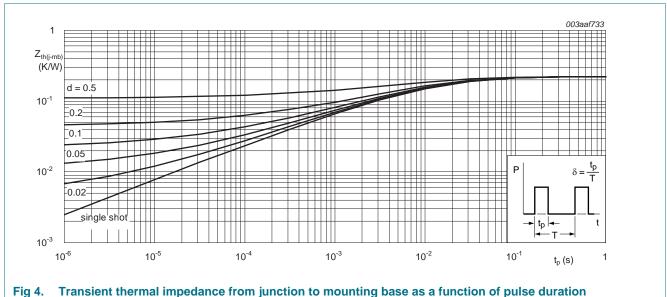
 $T_{mb} = 25~^{\circ}\mathrm{C}; I_{DM}\mathrm{is}$  a single pulse; Capped at 120 A due to package

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## **Thermal characteristics**

Table 5. **Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.44	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W



# 6. Characteristics

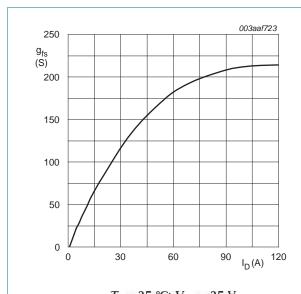
Table 6. Characteristics

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	racteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	100	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = -55 \text{ °C}$ ; see <u>Figure 10</u>	-	-	4.6	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; see <u>Figure 10</u>	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
DSS	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.08	10	μΑ
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 175 °C	-	-	500	μΑ
GSS	gate leakage current	V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	10	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 °C;$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	12	14	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	7.7	9	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	1] _	4.3	5	mΩ	
$R_{G}$	gate resistance	f = 1 MHz	-	0.9	-	Ω
Dynamic o	characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 75 \text{ A}$ ; $V_{DS} = 50 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	170	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	140	-	nC
$Q_{GS}$	gate-source charge	$I_D = 75 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$	-	48	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	31	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	17.3	-	nC
$Q_{GD}$	gate-drain charge		-	49	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V <sub>DS</sub> = 50 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	5.1	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	9900	-	pF
Coss	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	660	-	pF
O <sub>rss</sub>	reverse transfer capacitance		-	381	-	pF
d(on)	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 0.67 \Omega; V_{GS} = 10 \text{ V};$	-	45	-	ns
r	rise time	$R_{G(ext)} = 4.7 \Omega$ ; $I_D = 75 A$ ; $T_j = 25 °C$	-	91	-	ns
d(off)	turn-off delay time		-	122	-	ns
f	fall time		-	63	_	ns

Table 6. Characteristics ... continued

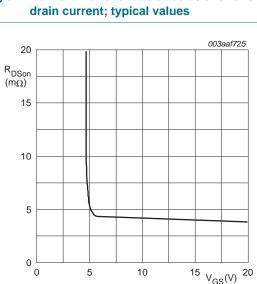
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drai	in diode					
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ;	-	75	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	235	-	nC

#### [1] Measured 3 mm from package.



 $T_j = 25$  °C;  $V_{DS} = 25$  V

Fig 5. Forward transconductance as a function of drain current: typical values



 $T_j = 25$  °C;  $I_D = 25$  A

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

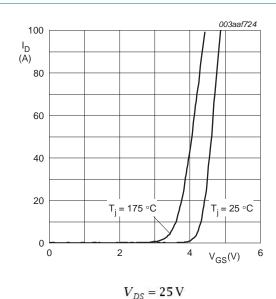
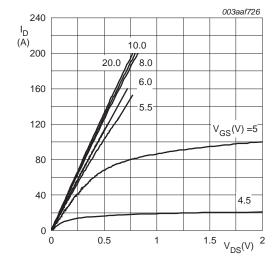


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25$  °C;  $t_p = 300 \,\mu s$ 

Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values

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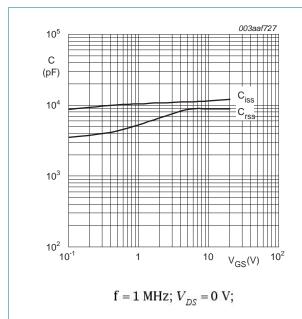


Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

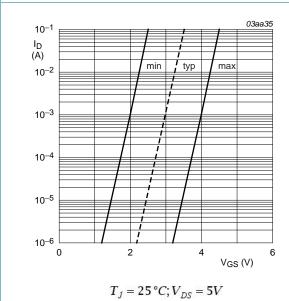


Fig 11. Sub-threshold drain current as a function of gate-source voltage

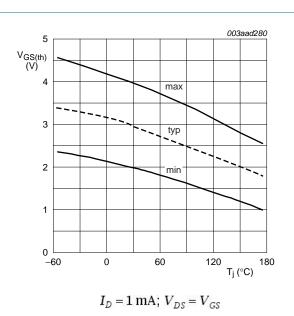


Fig 10. Gate-source threshold voltage as a function of junction temperature

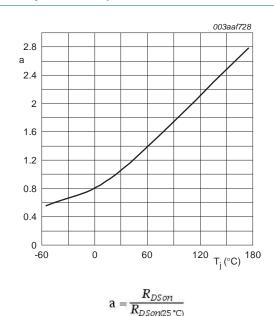


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

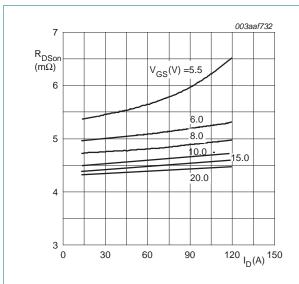


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

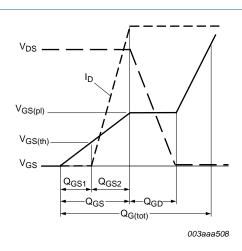


Fig 14. Gate charge waveform definitions

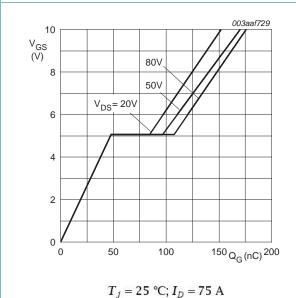


Fig 15. Gate-source voltage as a function of gate charge; typical values

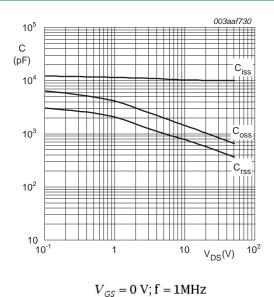


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

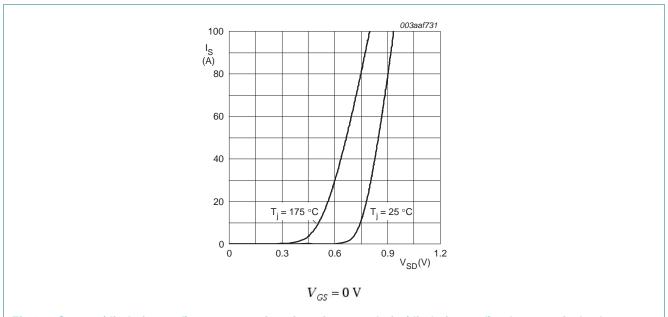


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

# 7. Package outline

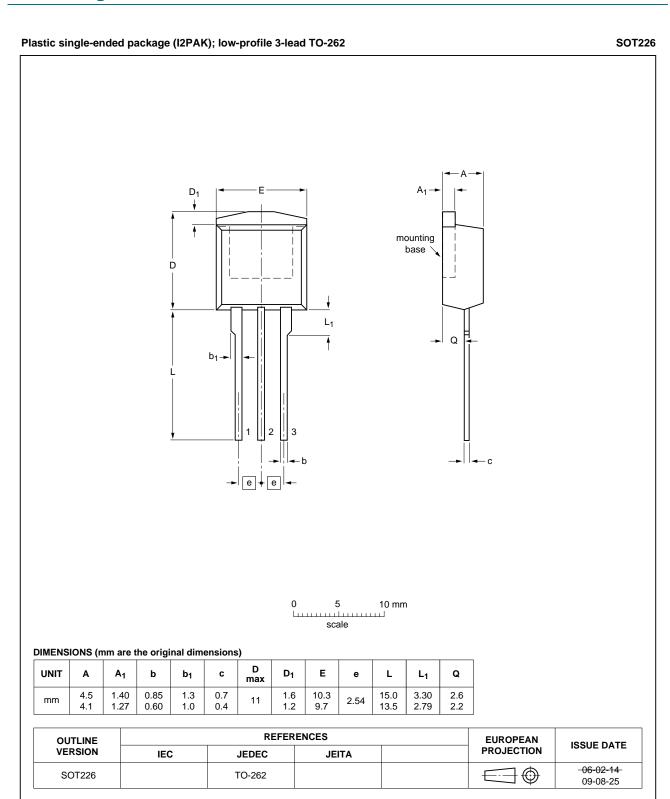


Fig 18. Package outline SOT226 (I2PAK)

# 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN5R0-100ES v.3	20110926	Product data sheet	-	PSMN5R0-100ES v.2
Modifications:	<ul> <li>Various changes to</li> </ul>	content.		
PSMN5R0-100ES v.2	20110415	Product data sheet	-	PSMN5R0-100ES v.1

## 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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